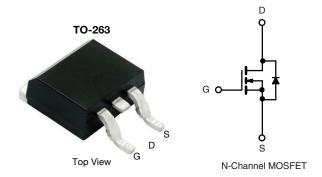


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Automotive N-Channel 300 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	300	
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.097	
I _D (A)	35	
Configuration	Single	
Package	TO-263	



FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ABSOLUTE MAXIMUM RATING	iS (T _C = 25 °C, unless	s otherwise noted	i)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	300	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C	1	35	
Continuous Drain Current	T _C = 125 °C	I _D	20	
Continuous Source Current (Diode Conduction) a		I _S	120	А
Pulsed Drain Current b			75	
Single Pulse Avalanche Current	1 0.1 ml l	I _{AS}	33	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	54	mJ
Marrian Danier Discipation h	T _C = 25 °C	Б	375	W
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	125	VV
Operating Junction and Storage Temperature	re Range	T _J , T _{stq}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	G/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	•	•					
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	300	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 300 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 300 V, T _J = 125 °C	-	-	50	μA
		V _{GS} = 0 V	V _{DS} = 300 V, T _J = 175 °C	-	-	1	mA
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 10 A	-	0.078	0.097	
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.214	Ω
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.285	
Forward Transconductance b	9fs	V _{DS}	= 15 V, I _D = 10 A	-	40	-	S
Dynamic ^b	•	·					
Input Capacitance	C _{iss}			-	4515	5650	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	320	400	pF
Reverse Transfer Capacitance	C _{rss}			-	146	185	
Total Gate Charge ^c	Qg			-	86	130	
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 150 \text{ V}, I_D = 9 \text{ A}$	-	16	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	28	-	
Gate Resistance	R _g		f = 1 MHz	0.3	0.75	1.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	20	30	
Rise Time ^c	t _r	$V_{DD} =$	150 V, R_L = 16.7 Ω	-	40	60	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 9 A$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	35	53	ns
Fall Time ^c	t _f		_	-	20	30	
Source-Drain Diode Ratings and Chara	acteristics ^b						
				_	_	75	Α
Pulsed Current ^a	I _{SM}					73	

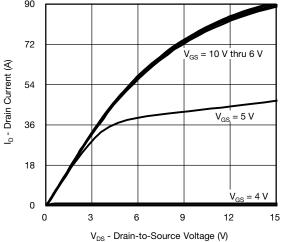
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

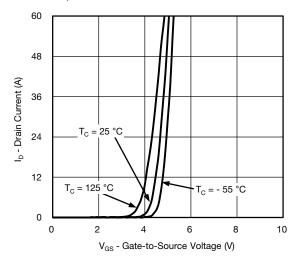


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

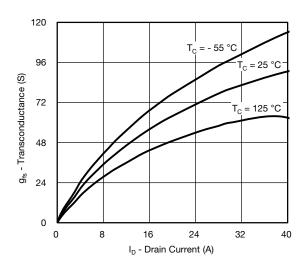




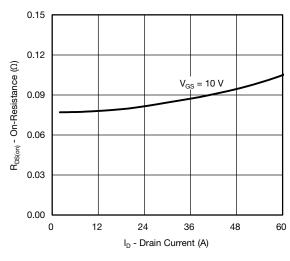
Output Characteristics



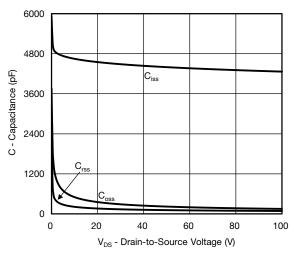
Transfer Characteristics



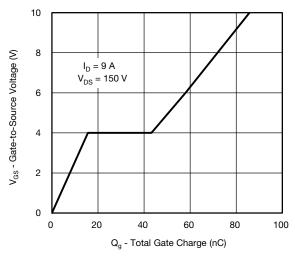
Transconductance



On-Resistance vs. Drain Current



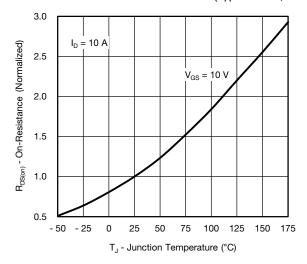
Capacitance

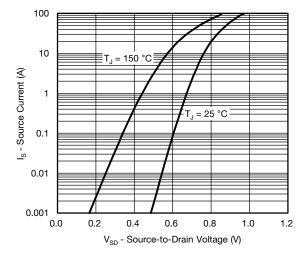


Gate Charge

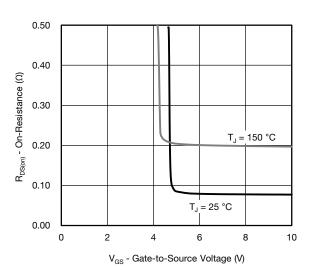


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

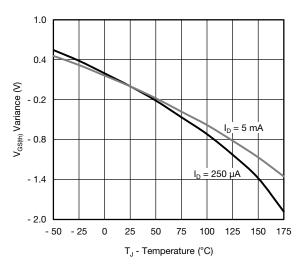




On-Resistance vs. Junction Temperature

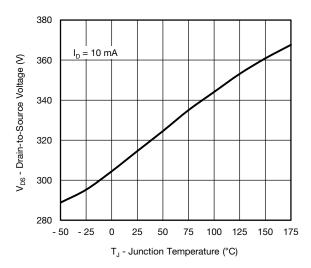


Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



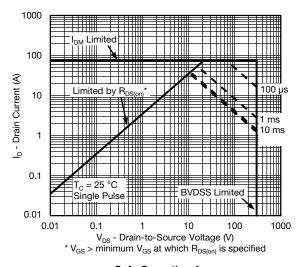


Drain Source Breakdown vs. Junction Temperature

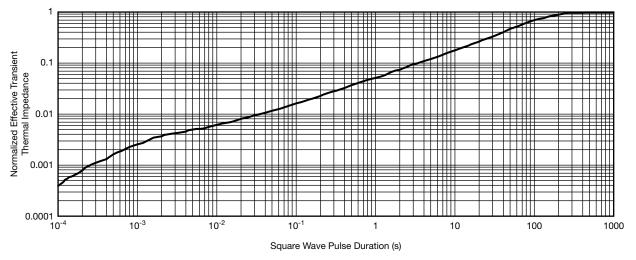
For technical questions, contact: automostech



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



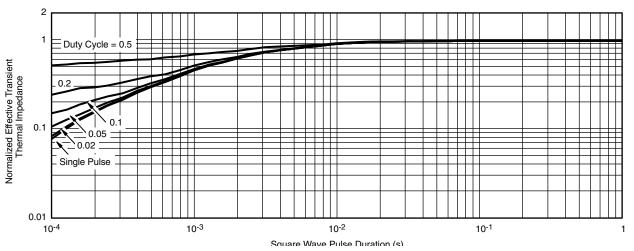
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg266742.



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REVISION HISTORY a				
REVISION	DATE	DESCRIPTION OF CHANGE		
В	04-Aug-15	Revised R _g minimum limit		

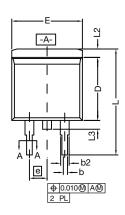
Note

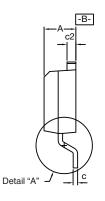
a. As of April 2014

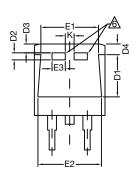
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TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T









DETAIL A (ROTATED 90°)



≥ <u>↓</u>			ţ
< T		10	ပ
SF	CTION	1	1

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

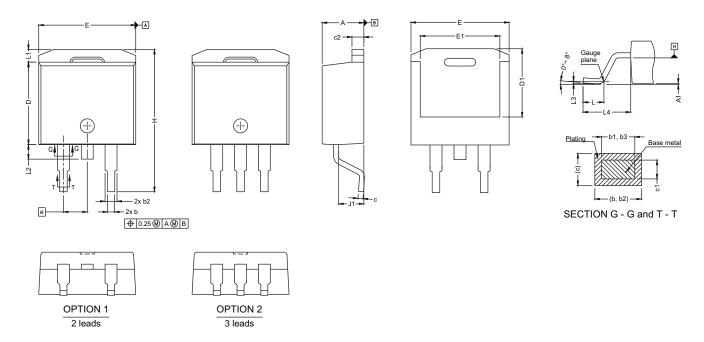
		INC	HES	MILLIMETERS		
	DIM.	MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
b		0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
C*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	<u>E1</u>	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100) BSC	2.54	BSC	
	K	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
	L3	0.050	0.070	1.270	1.778	
	L4	0.010	BSC	0.254	BSC	
	М	-	0.002	-	0.050	



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VERSION 2: FACILITY CODE = N



DIM.	MIN.	MAX.	
A	4.36	4.56	
A1	0	0.25	
b	0.70	0.90	
b1	0.51	0.89	
b2	1.20	1.46	
b3	1.17	1.37	
С	0.38	0.694	
c1	0.38	0.534	
c2	1.19	1.34	
D	8.60	9.00	
D1	6.9	7.5	
E	10.15	10.55	
E1	8.1	8.7	
е	2.54	BSC	
Н	15.0	15.6	
L	1.9	2.5	
L1	-	1.65	
L2	-	1.78	
L3	0.25	5 typ.	
L4	4.78	5.28	
J1	2.56	2.96	

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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